## DSC2A01

### Silicon NPN epitaxial planar type

For low frequency amplification

#### ■ Features

- $\bullet$  High forward current transfer ratio  $h_{\text{FE}}$  with excellent linearity
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

#### ■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	40	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	15	V
Collector current	$I_{C}$	50	mA
Peak collector current	I <sub>CP</sub>	100	mA
Collector power dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### ■ Package

• Code

Mini3-G3-B

- Pin Name
  - 1. Base
  - 2. Emitter
  - 3. Collector
- Marking Symbol: C8

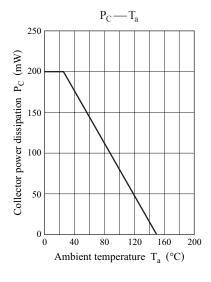
### ■ Electrical Characteristics $T_a = 25$ °C±3°C

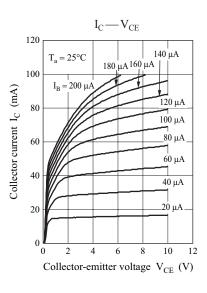
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	40			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 10 \mu A, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 20 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2000	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz

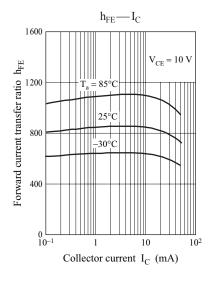
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

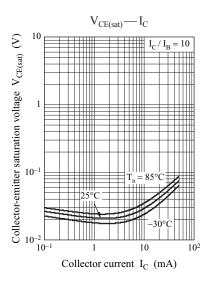
#### 2. \*: Rank classification

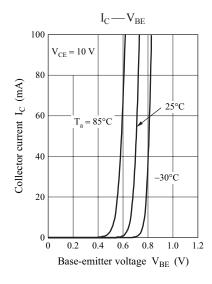
Code	R	S	T
Rank	R	S	Т
$h_{\mathrm{FE}}$	400 to 800	600 to 1200	1000 to 2000
Marking Symbol	C8R	C8S	C8T

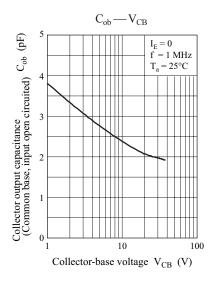


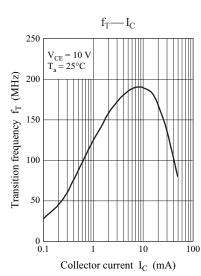








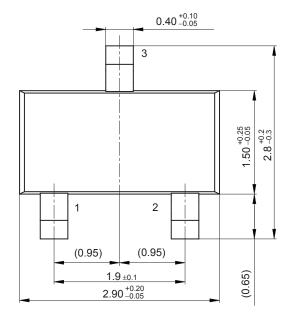


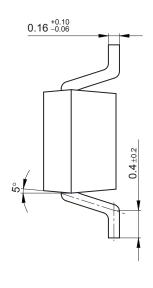


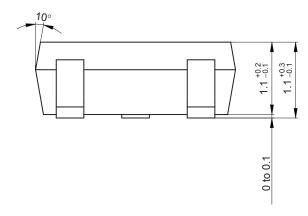
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Mini3-G3-B









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